

IN THE CLAIMS

Please amend the claims as follows.

1. (Amended) A method of forming a trench in a semiconductor device, comprising:
  - disposing a masking material on the semiconductor device;
  - forming a protruding portion at a location of the trench by forming an opening in the masking material adjacent to the location of the trench;
  - depositing a semiconductor material to fill in the opening; [ and]
  - removing the protruding portion to form the trench; and
  - etching the semiconductor material to round off corners of the trench.
2. (Amended) The method of claim 1, further include[es]ing:
  - providing a substrate supporting the masking material;
  - and
  - forming a first epi layer between the substrate and the masking material.

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9. (Amended) A method of forming a trench in a semiconductor device, comprising:

providing a substrate for the semiconductor device;

forming a first epi layer above the substrate and having a major surface;

forming a protruding region on the first epi layer having an opening adjacent to the protruding region and exposing the major surface of the first epi layer;

forming a second epi layer within the opening adjacent to the protruding region; [ and]

removing the protruding region to form the trench within the second epi layer aligned with the major surface of the first epi layer of the semiconductor device; and

etching the second epi layer to round off corners of the trench.

17. (Amended) A method of forming a trench in a semiconductor device, comprising;

disposing a first material on the semiconductor device;

forming first and second openings in the first material to form a protruding region; [ and]

disposing a second material in the first and second openings; [ and]

removing the protruding region to form the trench; and

etching the second material to round off corners of the trench.

25. (Amended) The method of claim 24, wherein disposing the second material over the protruding region includes using a blanket epi growth process.

Cancel claims 26-27 without prejudice to their subject matter.

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